NEC

NPN SILICON TRANSISTOR 2SC1841

DESCRIPTION

The 2SC1841 is designed for use in AF amplifier, driver and

low speed switching.

FEATURES

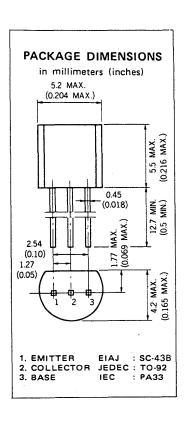
• High Voltage V_{CEO}: 120 V

High h_{FE}

 h_{FE} : 600 TYP. $(V_{CE} = 6.0 \text{ V}, I_{C} = 1.0 \text{ mA})$

ABSOLUTE MAXIMUM RATINGS

MOM MATMES
Maximum Temperatures
Storage Temperature55 to +125 °C
Junction Temperature +125 °C Maximur
Maximum Power Dissipation (Ta = 25 °C)
Total Power Dissipation 500 mV
Maximum Voltages and Currents (Ta = 25 °C)
V _{CBO} Collector to Base Voltage 120 V
VCEO Collector to Emitter Voltage 120 V
VEBO Emitter to Base Voltage 5.0 V
IC Collector Current 50 m/
IB Base Current



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE1	DC Current Gain	150	580			$V_{CE} = 6.0 \text{ V}, I_{C} = 0.1 \text{ mA}$
hFE2	DC Current Gain	200	600	1200		$V_{CE} = 6.0 \text{ V, } I_{C} = 1.0 \text{ mA}$
fT	Gain Bandwidth Product	50	110		MHz	$V_{CE} = 6.0 \text{ V}, I_{E} = -1.0 \text{ mA}$
C _{ob}	Output Capacitance		1.6	2.5	рF	$V_{CB} = 30 \text{ V, } I_E = 0, f = 1.0 \text{ MHz}$
Ісво	Collector Cutoff Current			50	nΑ	V _{CB} = 120 V, I _E = 0
IEBO	Emitter Cutoff Current			50	nΑ	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$
VBE	Base to Emitter Voltage	550	590	650	mV	$V_{CE} = 6.0 \text{ V, } I_{C} = 1.0 \text{ mA}$
VBE(sat)	Base Saturation Voltage		0.73	1.0	V	I _C = 10 mA, I _B = 1.0 mA
V _{CE(sat)}	Collector Saturation Voltage		70	300	mV	I _C = 10 mA, I _B = 1.0 mA

Classification of h_{FE2}

Rank P		F	E	U
Range	200 – 400	300 - 600	400 - 800	600 - 1200

 h_{FE} Test Conditions : $V_{\text{CE}} = 6.0 \text{ V}$, $I_{\text{C}} = 1.0 \text{ mA}$

TYPICAL CHARACTERISTICS (Ta = 25 °C unless otherwise noted)

